FAIRCHILD SEMICONDUCTOR®

September 2010

# FDMC7672S

## N-Channel Power Trench® SyncFET™

**30 V, 14.8 A, 6.0 mΩ**

### Features

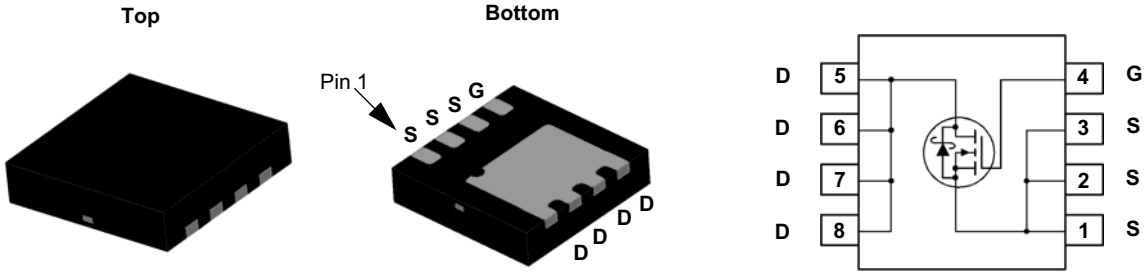
- Max $r_{DS(on)}$ = 6.0 mΩ at $V_{GS}$ = 10 V, $I_D$ = 14.8 A
- Max $r_{DS(on)}$ = 7.1 mΩ at $V_{GS}$ = 4.5 V, $I_D$ = 12.4 A
- High performance technology for extremely low $r_{DS(on)}$
- Termination is Lead-free and RoHS Compliant

### General Description

This FDMC7672S is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery packs.

### Applications

- DC - DC Buck Converters
- Notebook battery power mangement
- Load switch in Notebook




MLP 3.3x3.3

## MOSFET Maximum Ratings $T_A$ = 25 °C unless otherwise noted

| Symbol | Parameter | | | Ratings | Units |
|---|---|---|---|---|---|
| $V_{DS}$ | Drain to Source Voltage | | | 30 | V |
| $V_{GS}$ | Gate to Source Voltage | | | ±20 | V |
| $I_D$ | Drain Current -Continuous (Package limited) | $T_C$ = 25 °C | | 18 | A |
| | -Continuous | $T_A$ = 25 °C | (Note 1a) | 14.8 | |
| | -Pulsed | | | 45 | |
| $E_{AS}$ | Single Pulse Avalanche Energy | | (Note 3) | 60 | mJ |
| $P_D$ | Power Dissipation | $T_C$ = 25 °C | | 36 | W |
| | Power Dissipation | $T_A$ = 25 °C | (Note 1a) | 2.3 | |
| $T_J$, $T_{STG}$ | Operating and Storage Junction Temperature Range | | | -55 to +150 | °C |

### Thermal Characteristics

| | | | |
|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 3.5 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 53 | °C/W |

### Package Marking and Ordering Information

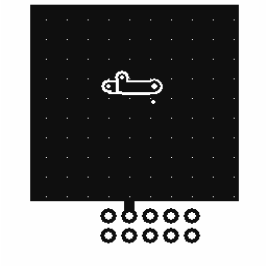
| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|---|---|---|---|---|---|
| FDMC7672S | FDMC7672S | MLP 3.3X3.3 | 13 ” | 12 mm | 3000 units |

## Electrical Characteristics $T_J$ = 25 °C unless otherwise noted

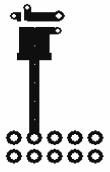
| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| $BV_{DSS}$ | Drain to Source Breakdown Voltage | $I_D$ = 1 mA, $V_{GS}$ = 0 V | 30 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D$ = 10 mA, referenced to 25 °C | | 12 | | mV/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 24 V, $V_{GS}$ = 0 V | | | 1 | mA |
| $I_{GSS}$ | Gate to Source Leakage Current | $V_{GS}$ = 20 V, $V_{DS}$ = 0 V | | | 100 | nA |
| **On Characteristics (Note 2)** | | | | | | |
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS}$ = $V_{DS}$, $I_D$ = 1 mA | 1.2 | 1.6 | 3.0 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D$ = 10 mA, referenced to 25 °C | | -6 | | mV/°C |
| $r_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS}$ = 10 V, $I_D$ = 14.8 A | | 5.0 | 6.0 | mΩ |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 12.4 A | | 6.1 | 7.1 | |
| | | $V_{GS}$ = 10 V, $I_D$ = 14.8 A, $T_J$ = 125 °C | | 5.9 | 9.0 | |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = 5 V, $I_D$ = 14.8 A | | 78 | | S |
| **Dynamic Characteristics** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 15 V, $V_{GS}$ = 0 V, f = 1 MHz | | 1895 | 2520 | pF |
| $C_{oss}$ | Output Capacitance | | | 770 | 1025 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 85 | 130 | pF |
| $R_g$ | Gate Resistance | | | 1.2 | 3.2 | Ω |
| **Switching Characteristics** | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD}$ = 15 V, $I_D$ = 14.8 A, $V_{GS}$ = 10 V, $R_{GEN}$ = 6 Ω | | 11 | 21 | ns |
| $t_r$ | Rise Time | | | 4 | 10 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 26 | 42 | ns |
| $t_f$ | Fall Time | | | 3 | 10 | ns |
| $Q_g$ | Total Gate Charge | $V_{GS}$ = 0 V to 10 V; $V_{DD}$ = 15 V, $I_D$ = 14.8 A | | 30 | 42 | nC |
| $Q_g$ | Total Gate Charge | $V_{GS}$ = 0 V to 4.5 V; $V_{DD}$ = 15 V, $I_D$ = 14.8 A | | 14 | 20 | nC |
| $Q_{gs}$ | Gate to Source Gate Charge | $V_{DD}$ = 15 V, $I_D$ = 14.8 A | | 5.3 | | nC |
| $Q_{gd}$ | Gate to Drain “Miller” Charge | | | 4.0 | | nC |
| **Drain-Source Diode Characteristics** | | | | | | |
| $V_{SD}$ | Source to Drain Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = 14.8 A (Note 2) | | 0.8 | 1.3 | V |
| | | $V_{GS}$ = 0 V, $I_S$ = 1.9 A (Note 2) | | 0.5 | 1.2 | |
| $t_{rr}$ | Reverse Recovery Time | $I_F$ = 14.8 A, di/dt = 300 A/μs | | 29 | 45 | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | | 28 | 44 | nC |

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in$^2$ pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 53 °C/W when mounted on a 1 in$^2$ pad of 2 oz copper.



b. 125 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.

3. $E_{AS}$ of 60 mJ is based on starting $T_J$ = 25 °C, L = 1 mH, $I_{AS}$ = 11 A, $V_{DD}$ = 27 V, $V_{GS}$ = 10 V. 100% test at L = 3 mH, $I_{AS}$ = 4.8 A.

## Typical Characteristics $T_J$ = 25 °C unless otherwise noted

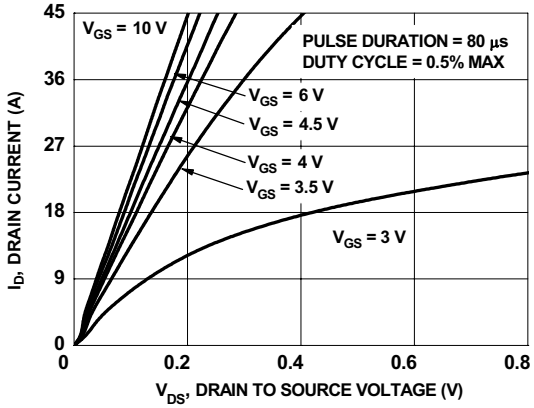



**Figure 1. On-Region Characteristics**

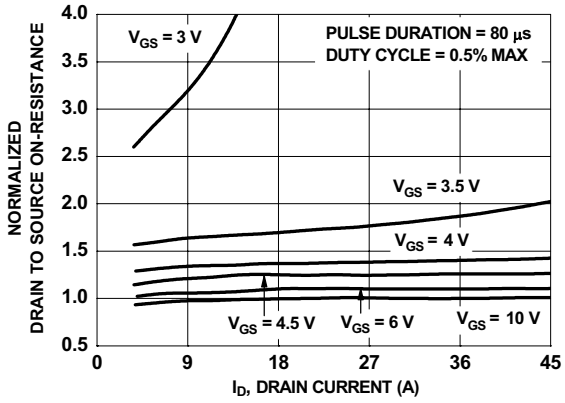



**Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage**

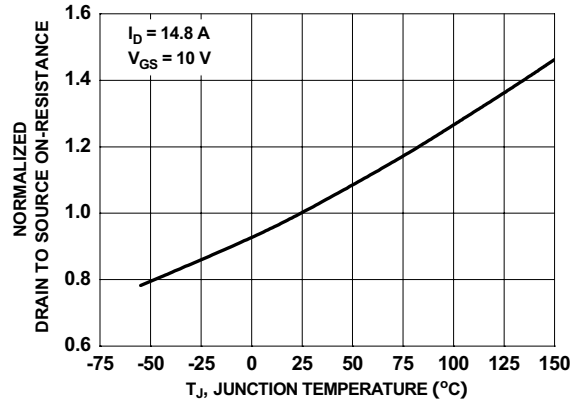



**Figure 3. Normalized On-Resistance vs Junction Temperature**

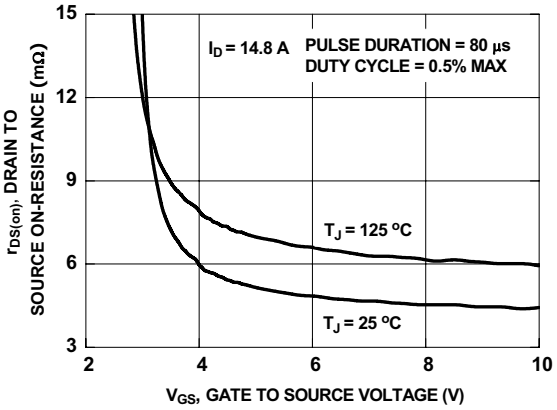



**Figure 4. On-Resistance vs Gate to Source Voltage**

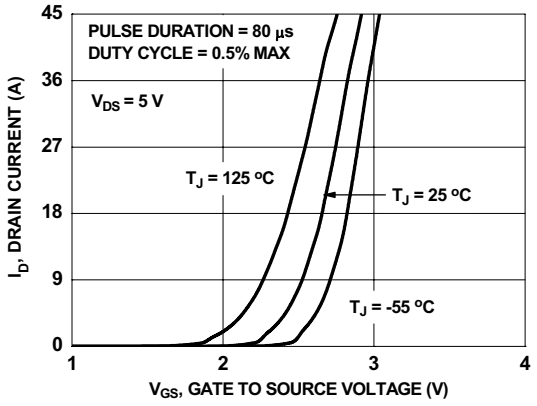



**Figure 5. Transfer Characteristics**

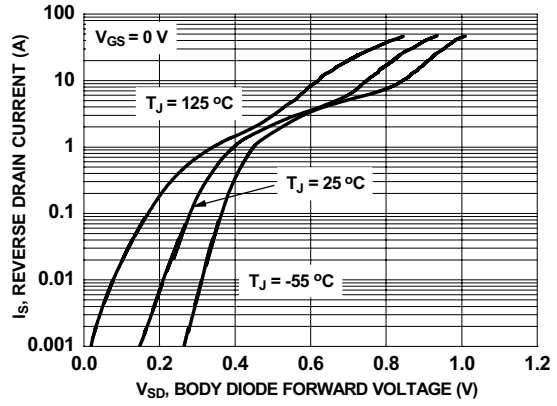



**Figure 6. Source to Drain Diode Forward Voltage vs Source Current**

## Typical Characteristics $T_J$ = 25 °C unless otherwise noted

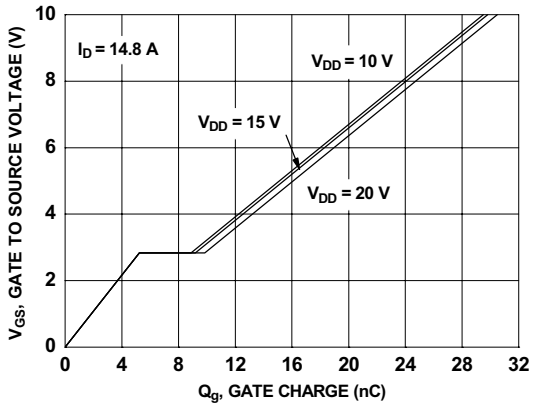



**Figure 7. Gate Charge Characteristics**

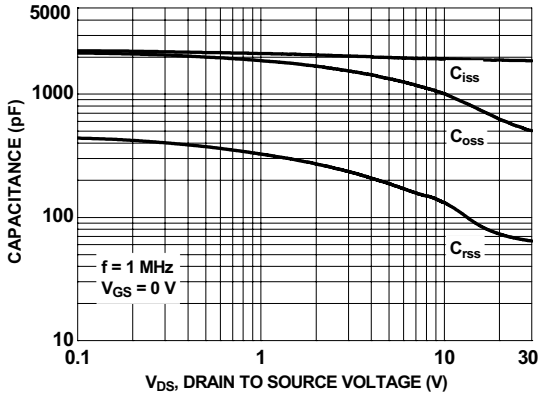



**Figure 8. Capacitance vs Drain to Source Voltage**

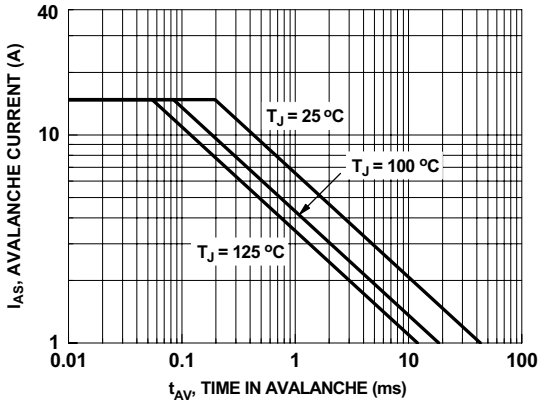



**Figure 9. Unclamped Inductive Switching Capability**

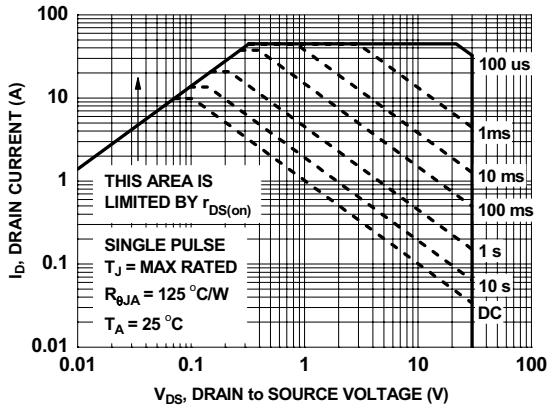



**Figure 10. Forward Bias Safe Operating Area**

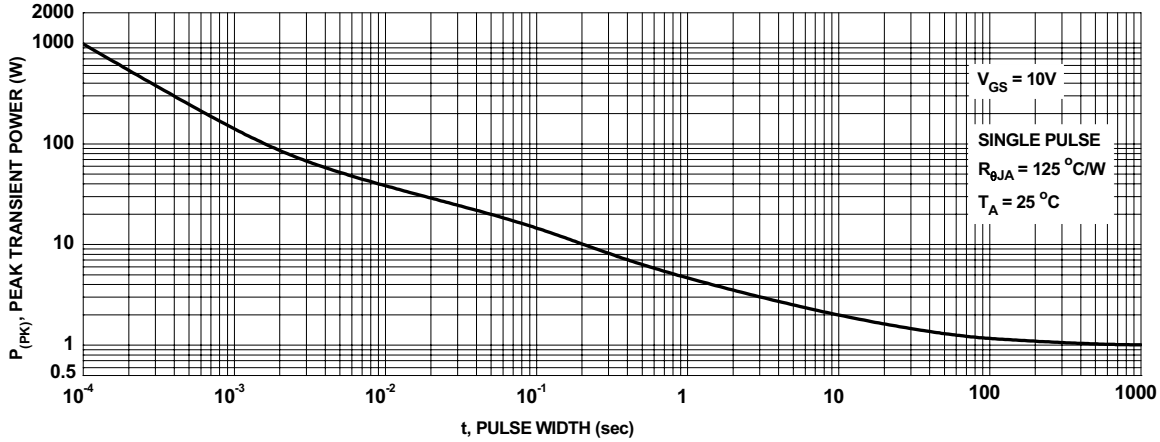



**Figure 11. Single Pulse Maximum Power Dissipation**

## Typical Characteristics $T_J$ = 25 °C unless otherwise noted

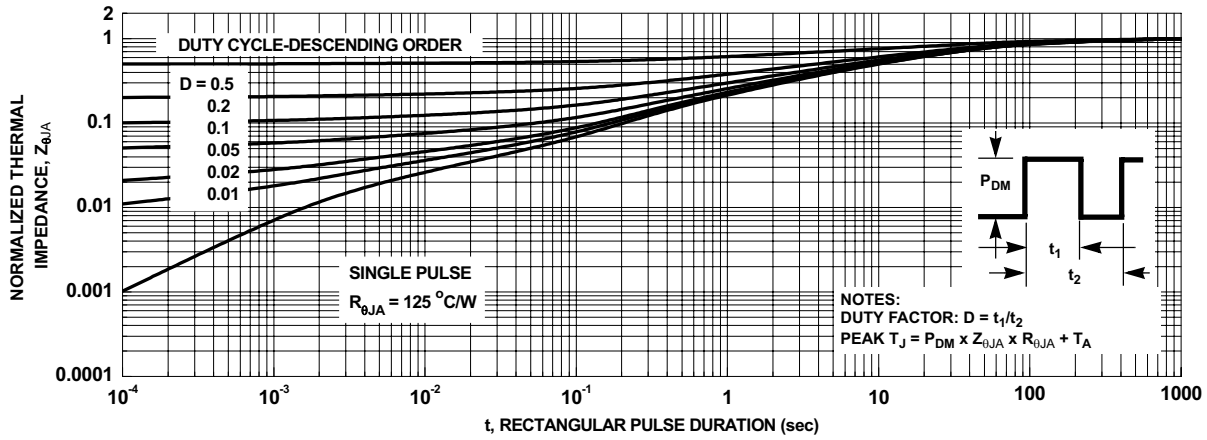



**Figure 12. Junction-to-Ambient Transient Thermal Response Curve**

## Typical Characteristics (continued)

### SyncFET Schottky body diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MoSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 13 shows the reverses recovery characteristic of the FDMC7672S.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

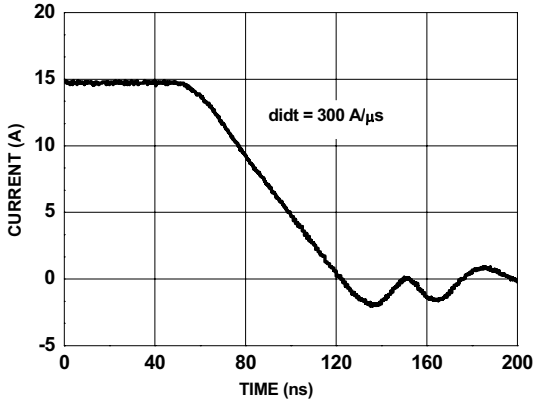



**Figure 13. SyncFET body diode reverse recovery characteristic**

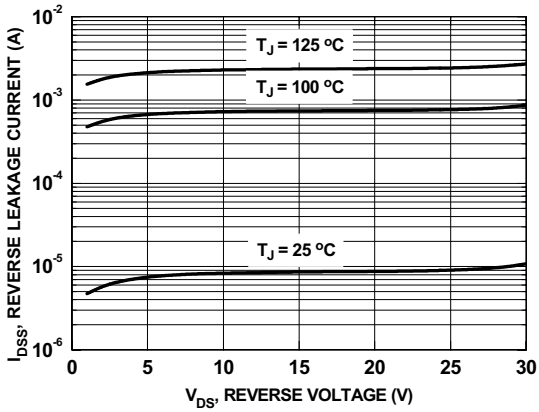
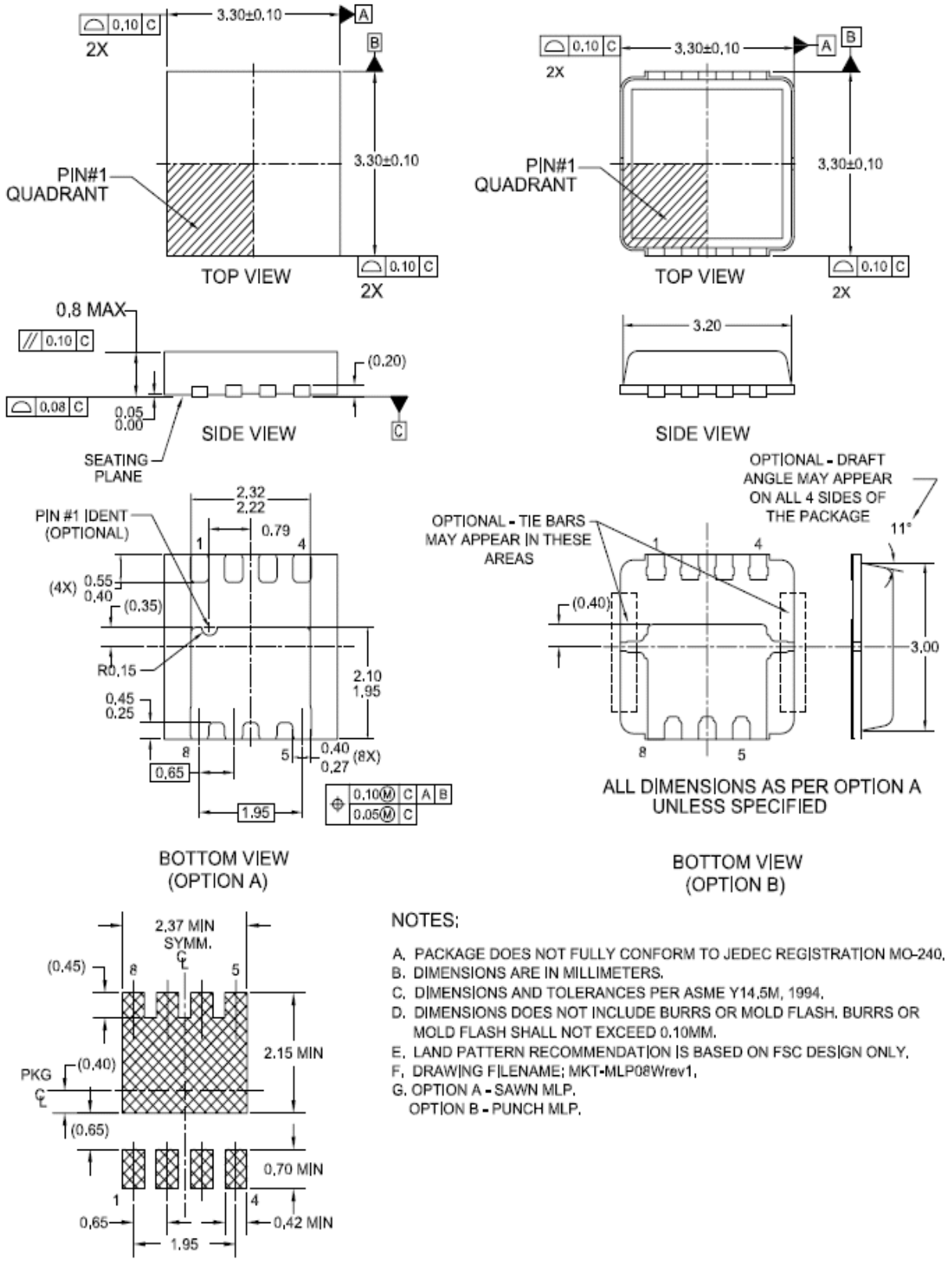



**Figure 14. SyncFET body diode reverses leakage versus drain-source voltage**

## Dimensional Outline and Pad Layout




NOTES:

A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-240.
B. DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
D. DIMENSIONS DOES NOT INCLUDE BURRS OR MOLD FLASH. BURRS OR MOLD FLASH SHALL NOT EXCEED 0.10MM.
E. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY.
F. DRAWING FILENAME: MKT-MLP08Wrev1.
G. OPTION A - SAWN MLP.
OPTION B - PUNCH MLP.

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